# 2SC3757

## Silicon NPN epitaxial planar type

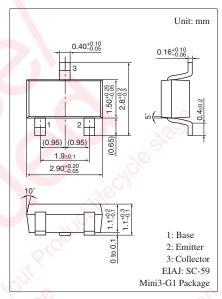
#### For high-speed switching

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	40	V	
Collector-emitter voltage (E-B short)	V <sub>CES</sub>	40	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	100	mA	
Peak collector current	$I_{CP}$	300	mA	
Collector power dissipation	P <sub>C</sub>	200	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



Marking Symbol: 2Y

### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

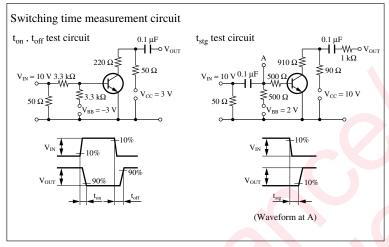
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 15 \text{ V}, I_{E} = 0$	10	350	0.1	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}, I_C = 0$	S ON	O	0.1	μΑ
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 1 \text{ V}, I_{C} = 10 \text{ mA}$	60		200	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.17	0.25	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$			1.0	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_{E} = -10 \text{ mA}, f = 200 \text{ MHz}$		450		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		2	6	pF
(Common base, input open circuited)		is wh				
Turn-on time	t <sub>on</sub>	Refer to the switching time measurement		17		ns
Turn-off time	t <sub>off</sub>	circuit		17		ns
Storage time	t <sub>stg</sub>			10		ns

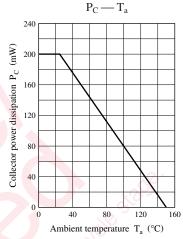
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

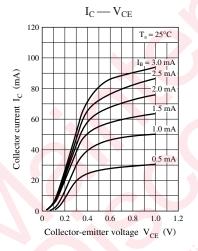
#### 2. \*: Rank classification

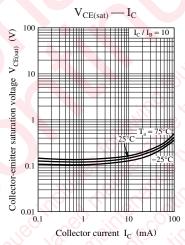
Rank	Q	R
$h_{FE}$	60 to 120	90 to 200

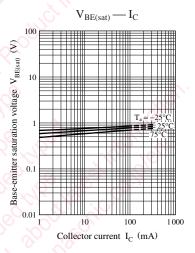
## **Panasonic**

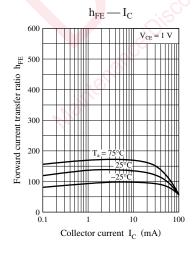


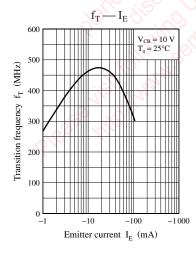


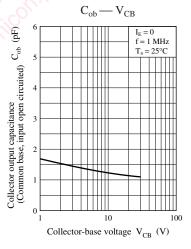












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